AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Original) A method for manufacturing a photomask blank having a film of at least one layer formed on a substrate, comprising the steps of forming a film on a substrate, and irradiating the film with light from a flash lamp.

2. (Original) The method of claim 1 wherein the step of forming a film on a substrate includes sputtering.

3. (Original) The method of claim 1 wherein the film of at least one layer has a lower light transmittance than the substrate.

4. (Original) The method of claim 1 wherein the film is a phase shift film.

5. (Original) The method of claim 4 wherein said phase shift film contains silicon, at least one metal other than silicon, and at least one element selected from the group consisting of oxygen, carbon and nitrogen.

6. (Original) A method for manufacturing a photomask comprising the steps of:

forming a patterned resist on the film on the photomask blank manufactured by the method of claim 1, by photolithography,

etching away those portions of the film which are not covered with the resist, and

removing the resist.

7. (New) The method of claim 1 wherein the light irradiates the entire surface of the film.

8. (New) The method of claim 7 wherein the step of forming a film on a substrate includes sputtering.

9. (New) The method of claim 7 wherein the film of at least one layer has a lower light transmittance than the substrate.

10. (New) The method of claim 7 wherein the film is a phase shift film.

11. (New) The method of claim 10 wherein said phase shift film contains silicon, at least one metal other than silicon, and at least one element selected from the group consisting of oxygen, carbon and nitrogen.

12. (New) A method for manufacturing a photomask comprising the steps of:

forming a patterned resist on the film on the photomask blank manufactured by the method of claim 7, by photolithography,

etching away those portions of the film which are not covered with the resist, and

removing the resist.

13. (New) The method of claim 1 wherein the substrate is a transparent substrate and the film is a phase shift film, a light-shielding film or an antireflection film.

14. (New) The method of claim 13 wherein the step of forming a film on a substrate includes sputtering.

15. (New) The method of claim 13 wherein the film of at least one layer has a lower light transmittance than the substrate.

16. (New) The method of claim 13 wherein the film is a phase shift film.

17. (New) The method of claim 16 wherein said phase shift film contains silicon, at least one metal other than silicon, and at least one element selected from the group consisting of oxygen, carbon and nitrogen.

18. (New) A method for manufacturing a photomask comprising the steps of:

forming a patterned resist on the film on the photomask blank manufactured by the method of claim 13, by photolithography,

etching away those portions of the film which are not covered with the resist, and

removing the resist.